L Number	Hits	Search Text	DB	Time stamp
1	2	6274488.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:26
2	17	("4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774").PN.	USPAT	2004/03/12 13:16
3	167	explosive with \$2crystallization	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:26
4	1188	gate same silicon same laser same amorphous	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:27
5	4	(explosive with \$2crystallization) and (gate same silicon same laser same amorphous)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:33
6	19	(explosive with \$2crystallization) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:52
7	421	(amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 16:34
8	41	((amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)) same laser	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 13:52
9	24	(((amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)) same laser) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 15:18
10	22	((((amorphous with silicon with gate) same (dop\$3 with amorphous) same (crystal or crystallization or crystalline or crystallized)) same laser) and 438/\$3.ccls.) and (@ad<20010829 or @rlad<20010829)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:52
11	4228	melting with temperature with (silicon ajd dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:00
12	201	melting with temperature with (silicon adj dioxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:00
13	8	("5405806"   "5432129"   "5624867"   "5861340"   "5888888"   "5953615"   "5981372"   "6365446").PN.	USPAT	2004/03/12 14:12
14	10	("5405806"   "5432129"   "5624867"   "5888888"   "5953615"   "5981372"   "6197646"   "6207563"   "6274511"   "6281102").PN.	USPAT	2004/03/12 14:14
15	21	(explosive with \$2crystallization) and (amorphous same dop\$3 same (crystal or crystallization or crystalline or crystallized))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 14:52
16	19	((explosive with \$2crystallization) and (amorphous same dop\$3 same (crystal or crystallization or crystalline or crystallized))) and (@ad<20010829 or @rlad<20010829)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/03/12 15:17

17	3	(explosive with \$2crystallization) same	USPAT;	2004/03/12
		gate	US-PGPUB;	15:04
	1		EPO; JPO;	
18	53	amayahaya gama gata gama maltan	DERWENT USPAT;	2004/02/12
10	] 53	amorphous same gate same molten	US-PGPUB;	2004/03/12 15:18
			EPO; JPO;	15.16
			DERWENT	1
19	18	(amorphous same gate same molten) and	USPAT;	2004/03/12
		438/\$3.ccls.	US-PGPUB;	15:18
	1		EPO; JPO;	1
			DERWENT	l i
20	1	(explosive with \$2crystallization) and	USPAT;	2004/03/12
		((amorphous with silicon with gate) same	US-PGPUB;	16:35
		(dop\$3 with amorphous) same (crystal or	EPO; JPO;	
		crystallization or crystalline or	DERWENT	
		crystallized))		
-	213204	257/\$3.ccls. or 438/\$3.ccls.	USPAT;	2004/03/12
			EPO; JPO;	13:14
		/257/621 420/621- \	DERWENT	3003/04/00
-	6	(257/\$3.ccls. or 438/\$3.ccls.) and insulat\$3 and radiat\$3 and (amorphous	USPAT;	2002/04/09
		near2 silicon) and crystall\$7 and	EPO; JPO; DERWENT	09.46
		explosive	DEVARENT	
_	1	(257/\$3.ccls. or 438/\$3.ccls.) and (xcr	USPAT;	2002/04/09
		or (explosive adj recrystallization)) and	EPO; JPO;	09:58
		irradiat\$3 and dopant and gate	DERWENT	
_	103	(257/\$3.ccls. or 438/\$3.ccls.) and	USPAT;	2002/04/09
		recrystallization and irradiat\$3 and	EPO; JPO;	09:59
		dopant and gate	DERWENT	
-	85	((257/\$3.ccls. or 438/\$3.ccls.) and	USPAT;	2002/04/09
		recrystallization and irradiat\$3 and	EPO; JPO;	15:19
		dopant and gate) and (amorphous adj	DERWENT	1
	_	silicon)	**********	
-	3	mosfet same (laser or irradiate) same	USPAT; EPO; JPO;	2002/04/09
		amorphous same (dopant or dope)	DERWENT	1 10:11
_	111	(laser or irradiate) same (amorphous adj	USPAT;	2002/04/10
		silicon) same (dopant or dope)	EPO; JPO;	16:52
		delicon, bame (depart of depe,	DERWENT	- 3 . 3
_	10	((laser or irradiate) same (amorphous adj	USPAT;	2002/04/09
		silicon) same (dopant or dope)) same	EPO; JPO;	16:14
		(insulat\$4 adj layer)	DERWENT	
-	241	mosfet with laser	USPAT;	2002/04/09
			EPO; JPO;	17:50
	_	/magfat with large) /	DERWENT	2002/04/00
-	2	(mosfet with laser) same (amorphous adj	USPAT; EPO; JPO;	2002/04/09
		51110011)	DERWENT	11:54
_	12	(mosfet with laser) same (dope dopant	USPAT;	2002/04/09
	•••	doped)	EPO; JPO;	18:06
			DERWENT	
-	42	(mosfet with laser) and ((dope dopant	USPAT;	2002/04/09
		doped) with gate)	EPO; JPO;	18:07
1			DERWENT	
1 -	12557	(mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
1		gate	EPO; JPO;	17:18
1	1.50	//manfat au fat au ma	DERWENT	2002/04/22
-	158	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
1		gate) same (laser or irradiation)	EPO; JPO; DERWENT	11:07
_	4	"5966605"	USPAT;	2002/04/10
			EPO; JPO;	11:07
1			DERWENT	
-	54793	gate with silicon	USPAT;	2002/04/10
1		-	EPO; JPO;	14:12
!			DERWENT	
-	6957	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
		gate) and (gate with silicon)	EPO; JPO;	14:12
	L		DERWENT	

- 2731					
Compared to the composition of the composition of the comparation of the composition of	-	15744	gate near2 silicon	•	1
-					14:12
Gate   and (gate near2 silicon)				DERWENT	
Compared to the composition of the composition of the compared to the compared to the composition of the c	-	2731		· ·	
			gate) and (gate near2 silicon)		14:12
Claser or irradiate)   Claser or irradiate   Claser or irradiate   Claser or irradiate	-	234		•	
110	1				14:15
gate) and (gate mear2 silicon)) and (laser or irradiate)) and amorphous and (recrystalline or crystalline)   13					
(laser or irradiate) and amorphous and (recrystalline)	-	110			
Crecrystalline or   13					16:15
13				DERWENT	
-   13					
B		1.2		110 D D M .	2002/04/10
B	-	13	"5937325"	· ·	
-   8					10:19
- 34	1_	۱	"6013028"		2002/04/10
		ľ	0013320	•	
34   (laser or irradiate) same (amorphous adj silicon) same ((doposition or evaporation))   (sputter or deposition or evaporation))   (mosfet or fet or mos) same dop\$3 same gate same (sputter or evaporat\$3 or deposit\$3)   (losefet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3)   (losefet or fet or mos) same dop\$3 same gate) same laser   (losefet or fet or mos) same dop\$3 same gate) same laser   (losefet or fet or mos) same dop\$3 same gate) same laser   (losefet or fet or mos) same dop\$3 same gate)   (losefet or fet or mos) same dop\$3 same gate) same laser   (losefet or fet or mos) same dop\$3 same gate)   (losefet or fet or mos) same dop\$3 same gate)   (losefet or fet or mos) same dop\$3 same gate)   (losefet or fet or mos) same dop\$3 same gate)   (losefet or fet or mos) same dop\$3 same gate)   (losefet or fet or mos) same losefet   (losefet or fet or mos) same losefet   (losefet or fet or mos) same losefet   (losefet or					10.20
Silicon  same ((dopant or dope  and (sputter or deposition or evaporation)  (mosfet or fet or mos) same dop\$3 same gate same (sputter or evaporat\$3 or deposit\$3) ((mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or deposit\$3 or evaporat\$3))	1_	34	(laser or irradiate) same (amorphous adi		2002/04/10
Sputter or deposition or evaporation   DERWINT (mosfet or fet or mos) same dop\$3 same gate same (sputter or evaporat\$3 or deposit\$3] (mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3) (mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3) (mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3) (mosfet or fet or mos) same dop\$3 same gate) and (dop\$3 with (sputter or evaporat\$3)) (mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter or evaporat\$3)) (mosfet or fet or mos) same dop\$3 same gate) same (dop\$3 with (sputter\$3 or evaporat\$3) (dop\$3 with (sputter\$3 or evaporat\$3) with silicon) and (mos or fet or mosfet) (dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same (mos or fet or mosfet) (dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same (mos or fet or mosfet) (dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same laser (dop\$3 with (sputter\$3 or evaporat\$3) (span) (dop\$3 with (sputter\$3 or evaporat\$3) (span) (dop\$3 with (sputter\$3 or evaporat\$3)) (span) (dop\$3 with (sputter\$3 or evaporat\$3) (span) (dop\$3 with (sputter\$3 or evaporat\$3)) (span) (dop\$3 with (span)					
3488					
Gate same (sputter or evaporat\$3 or deposit\$3)	-	3488			2002/04/10
deposit\$3]   dep					1
3958				· ·	
gate) and (dop\$3 with (sputter or deposits 30 or evaporat\$3))	-	3958			2002/04/10
deposits3 or evaporat\$3)   DERWENT			gate) and (dop\$3 with (sputter or	EPO; JPO;	17:21
gate   and (dop\$3 with (sputter or evaporat\$3))   (mosfet or fet or mos) same dop\$3 same   gate) same (dop\$3 with (sputter or evaporat\$3))   (mosfet or fet or mos) same dop\$3 same   gate) same (dop\$3 with (sputter or evaporat\$3))   (mosfet or fet or mos) same dop\$3 same   gate) same (dop\$3 with (sputter\$3 or evaporat\$3))   (dop\$3 with (sputter\$3 or evaporat\$3)   (dop\$3 with (sputter\$3 or evaporat\$3))   (dop\$3 with (sputter\$3 or evaporat\$3)   (dop\$3 with (sputter\$3 or evaporat\$3))   (dop\$3 with (sputter\$3 or evaporat\$3)   (dop\$3 wit				DERWENT	
Evaporat\$3)	-	137	((mosfet or fet or mos) same dop\$3 same	USPAT;	2002/04/10
1					17:21
gate   same   (dop\$3 with (sputter or evaporat\$3))   (mosfet or fet or mos) same dop\$3 same   gate) same   (dop\$3 with (sputter\$3 or evaporat\$3)   (dop\$3 with (sputter\$3 or evaporat\$3)   with silicon) and (mos or fet or mosfet)   USPAT;   2002/04/10   EPO; JPO;   DERWENT   USPAT;   2002/04/10   USPAT;   2002/04/11   USPAT;   2002/04/15   USPAT;   2					
evaporat\$3)	-	41		· ·	1
Total Compose					17:25
gate   same   dop\$3 with (sputter\$3 or evaporat\$3)   Cop\$3 with (sputter\$3 or evaporat\$3)   USPAT;   2002/04/10   USPAT;   2002/04/11   USPAT;   2002/04/15   USPAT;   2002/04					0000/04/10
-   320   (dop\$3 with (sputter\$3 or evaporat\$3)   USPAT;   2002/04/10   17:46   DERWENT   USPAT;   2002/04/10   17:46   DERWENT   USPAT;   2002/04/10   17:35   DERWENT   USPAT;   2002/04/10   DERWENT   USPAT;   EPO; JPO;   DERWENT   EPO; JPO;   DERWE	-	75			
320					11:32
with silicon) and (mos or fet or mosfet)   EPO; JPO; DERWENT   DERWENT   USPAT;   2002/04/10   17:35   DERWENT   USPAT;   2002/04/10   17:35   DERWENT   USPAT;   2002/04/10   DERWENT   USPAT;   2002/04/11   DERWENT   USPAT;   2002/04/15   DERWENT   2		200	evaporat\$3))		2002/04/10
DERWENT   USPAT;	-	320		,	
35			With Silicon) and (mos of let of moslet)		17.40
With silicon   Same (mos or fet or mosfet)   EPO; JPO; DERWENT   2002/04/10   With silicon   Same laser   EPO; JPO; DERWENT   2002/04/10   EPO; JPO; DERWENT   2002/04/10   EPO; JPO; DERWENT   EPO; JPO; DE	_	35	(don\$3 with (sputter\$3 or evaporat\$3)		2002/04/10
DERWENT		33			1 1
- 28 (dop\$3 with (sputter\$3 or evaporat\$3) with silicon) same laser  - 190 (dop\$3 with (sputter\$3 or evaporat\$3))					=
With silicon   Same laser   EPO; JPO; DERWENT   USPAT; 2002/04/10   Same laser   USPAT; 2002/04/10   Same laser   USPAT; 2002/04/10   Same laser   USPAT; 2002/04/10   Sepo; JPO; DERWENT   USPAT; 2002/04/10   Sepo; JPO; DERWENT   USPAT; 2002/04/10   Sepo; JPO; DERWENT   USPAT; 2002/04/11   Sepo; JPO; DERWENT   USPAT; 2002/04/15   Sepo; JPO; DERWENT   USPAT; 2002	_	28	(dop\$3 with (sputter\$3 or evaporat\$3)	USPAT;	2002/04/10
- 190 (dop\$3 with (sputter\$3 or evaporat\$3)) same laser  - 2 "6165875"					
Same laser   EPO; JPO; DERWENT   USPAT;   2002/04/10   EPO; JPO; DERWENT   USPAT;   2002/04/10   EPO; JPO; DERWENT   USPAT;   2002/04/11   IT: 34					
Same laser   EPO; JPO; DERWENT   USPAT;   2002/04/10   EPO; JPO; DERWENT   USPAT;   2002/04/10   EPO; JPO; DERWENT   USPAT;   2002/04/11   IT: 34	-	190	(dop\$3 with (sputter\$3 or evaporat\$3))	USPAT;	2002/04/10
- 2848 gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser and mosfet (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser and mosfet (gate with (metal or cap or capped) with (tungsten) (tungsten or tantalum or titanium or EPO; JPO; platinum)) and laser and mosfet (gatewith (gat				EPO; JPO;	18:02
2848   gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)   Gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)   and laser   Gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)   and laser   Gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)   and laser and mosfet   Gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)   and laser and mosfet   Gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)   and laser and mosfet   Gate with (metal or cap or capped) with (tungsten or tantalum or titanium or gate with (metal or cap or capped) with (tungsten or tantalum or titanium or USPAT;   2002/04/11   16:20   16:20   16:20   17:34   17					
- 2848 gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)  - 331 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser  - 89 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser or tantalum or titanium or platinum)) and laser and mosfet  - 4 "6077758"  - 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)	-	2	"6165875"		
- 2848 gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)  - 331 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser  - 89 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser and mosfet  - 4 "6077758"  - 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)					18:02
(tungsten or tantalum or titanium or platinum)  (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser  89 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser  (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum)) and laser and mosfet  4 "6077758"  11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or				1	0000/04/55
platinum) (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser  89 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser  40 (tungsten or tantalum or titanium or platinum) ) and laser and mosfet  40 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)	-	2848			
- 331 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser  - 89 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser and mosfet  - 4 "6077758"  - 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)				i '	10:14
(tungsten or tantalum or titanium or platinum) and laser  (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) and laser and mosfet  "6077758"  11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)		331			2002/04/11
platinum) ) and laser  (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser and mosfet  4 "6077758"  11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  12 ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)	-	331			1 ' '
- 89 (gate with (metal or cap or capped) with (tungsten or tantalum or titanium or platinum) ) and laser and mosfet  - 4 "6077758"  - 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  - 12 ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)					10.20
(tungsten or tantalum or titanium or platinum) ) and laser and mosfet  - 4 "6077758"  - 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus)	1_	90		1	2002/04/11
platinum   ) and laser and mosfet	_	09			
- 4 "6077758" USPAT; 2002/04/11 JPO; 17:34  - 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3)  - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02		1			10.20
- 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3) - 12 ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02	_	ا ۵			2002/04/11
- 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3) - 12 ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02		1	33.7700		
- 11867 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or evaporat\$3) - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02				· ·	
phosphorus) with (sputter\$3 or CVD or evaporat\$3)  12 ((boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02	_	11867	(boron or indium or arsenic or		2002/04/15
evaporat\$3) - 12 (boron or indium or arsenic or phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02				· ·	1
- 12 ((boron or indium or arsenic or USPAT; 2002/04/15 phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02					
phosphorus) with (sputter\$3 or CVD or EPO; JPO; 14:02	-	12			2002/04/15
					1
evaporat\$3)) same dopant same laser DERWENT				DERWENT	

-	1098	((boron or indium or arsenic or	USPAT;	2002/04/15
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:10
		or CVD or evaporat\$3)	DERWENT	
<del>-</del>	33	(((boron or indium or arsenic or	USPAT;	2002/04/15
		phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	14:09
		or CVD or evaporat\$3)) same dopant		14.05
			DERWENT	0000/04/15
-	239	((boron or indium or arsenic or	USPAT;	2002/04/15
	!	phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:13
		or CVD or evaporat\$3) with surface	DERWENT	
_	46	(((boron or indium or arsenic or	USPAT;	2002/04/15
	'	phosphorus) near2 layer) with (sputter\$3	EPO; JPO;	15:14
				12.14
		or CVD or evaporat\$3) with surface) and	DERWENT	
		laser		
-	2	5966605.pn.	USPAT;	2002/09/13
		-	EPO; JPO;	13:14
İ			DERWENT	
ŀ	2	6265476 mm	USPAT;	2002/09/13
-		6365476.pn.		· · ·
			EPO; JPO;	13:15
			DERWENT	
-	2	6274488.pn.	USPAT;	2002/09/13
	_	•	EPO; JPO;	13:16
1			DERWENT	- ·
		6077750		2002/00/13
-	2	6077758.pn.	USPAT;	2002/09/13
			EPO; JPO;	13:16
			DERWENT	
-	1175	radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5	EPO; JPO;	12:17
			DERWENT	
				1 2002 /12 /08
-	34	radiat\$3 same amorphous same silicon same	USPAT;	2002/12/08
		dop\$3 same crystalliz\$5	EPO; JPO;	12:12
•			DERWENT	
_	12	(radiat\$3 same amorphous same silicon	USPAT;	2002/12/08
		same dop\$3 same crystalliz\$5) same gate	EPO; JPO;	12:12
		Same dopps same organization same gard	DERWENT	]
	250			2002/12/08
-	350	radiat\$3 and amorphous and silicon and	USPAT;	
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:22
		dop\$3)	DERWENT	
_	315	(radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:20
		dop\$3)) and laser	DERWENT	1 -,
	1 101		1	2002/12/08
-	181	((radiat\$3 and amorphous and silicon and	USPAT;	
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:21
	ļ	dop\$3)) and laser) and 438/\$3.ccls.	DERWENT	
_	181	(((radiat\$3 and amorphous and silicon and	USPAT;	2002/12/08
		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:21
		dop\$3)) and laser) and 438/\$3.ccls.) and	DERWENT	
		dop\$377 and lase17 and 4307\$3.0013.7 and		
		1	таръш.	2002/12/00
1 -	33	· · · · · · · · · · · · · · · · · · ·	USPAT;	2002/12/08
1		dop\$3 and crystalliz\$5 and (gate with	EPO; JPO;	12:59
		dop\$3 with amorphous)	DERWENT	
-	4		USPAT;	2002/12/08
	_	dop\$3 with amorphous)	EPO; JPO;	13:04
		aopto aton amorbioas,	DERWENT	
	_			1 2002 /12 /09
-	2	radiat\$3 same amorphous same	USPAT;	2002/12/08
		(crystalliz\$5 with gate with dop\$3)	EPO; JPO;	13:08
			DERWENT	
-	11	radiat\$3 same amorphous same crystalliz\$5	USPAT;	2002/12/08
	Ī	same (gate with dop\$3)	EPO; JPO;	13:30
		, , , , , , , , , , , , , , , , , , , ,	DERWENT	
1_	28	anneals came crustallizes came	USPAT;	2002/12/08
1 -	28	anneal\$3 same crystalliz\$5 same	l '	
		(amorphous with gate with dop\$3)	EPO; JPO;	15:51
1			DERWENT	
-	3	("5872761"   "5994179"   "6054355").PN.	USPAT	2002/12/08
1	1			14:00
1 -	11	gate with height with "500" with	USPAT;	2002/12/08
	1 **		EPO; JPO;	15:55
1		(nanometer\$1 or nm)		1 -3.33
	]		DERWENT	1 0000 (00 (00
] -	62	gate with height with ("400" or "300" or	USPAT;	2002/12/08
	1	"200" or "100") with (nanometer\$1 or nm)	EPO; JPO;	15:56
1	1		DERWENT	

_	2	6159782.pn.	USPAT; EPO; JPO;	2003/06/03 14:19
-	144	xcr or (explosive adj \$2crystalliz\$4)	DERWENT USPAT; US-PGPUB;	2003/06/30 15:59
-	0	(xcr or (explosive adj \$2crystalliz\$4)) and (laser same amorphous same (polycrystalline or polysilicon))	EPO; JPO; DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/30 15:57
-	127	xcr and @ad<20010829	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/30 16:00
-	0	(xcr and @ad<20010829) and laser and amorphous and (polycrystalline or polysilicon) and (dopant or boron)	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/30 15:58
-	138	xcr	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/30 15:58
-	0	(xcr and @ad<20010829) and 438/\$3.ccls.	DERWENT USPAT; US-PGPUB; EPO; JPO;	2003/06/30 15:59
-	6	explosive adj \$2crystalliz\$4	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:59
-	35	explosive adj \$2crystalliz\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 15:59
-	16	(explosive adj \$2crystalliz\$5) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:42
-	15	((explosive adj \$2crystalliz\$5) and 438/\$3.ccls.) and @ad<20010829	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 17:46
-	18	("4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774"   "6274488").PN.	USPAT	2003/06/30 16:02
-	10	("4151008"   "4456490"   "4617066"   "5756369"   "5897381"   "5908307"   "5923963"   "5989966"   "6153483"   "6188106").PN.	USPAT	2003/06/30 16:10
-	17	"4522845"   "4622735"   "4683645"   "4830971"   "4924294"   "4931353"   "5010032"   "5122479"   "5236865"   "5302538"   "5405806"   "5563100"   "5593923"   "5888888"   "6060392"   "6072222"   "6174774").PN.	USPAT	2003/06/30 16:23
-	646		USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:40
-	277	(laser same gate same dop\$3 same silicon) same amorphous	USPAT; US-PGPUB; EPO; JPO;	2003/06/30 16:41
-	80	((laser same gate same dop\$3 same silicon) same amorphous) same temperature	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/30 16:41
L	1	I	Tankania T	[

-	74	(((laser same gate same dop\$3 same	USPAT;	2003/06/30
		silicon) same amorphous) same	US-PGPUB;	17:51
		temperature) and @ad<20010829	EPO; JPO;	
	41	////lagor game gate game dené? game	DERWENT USPAT;	2003/06/30
-	41	((((laser same gate same dop\$3 same   silicon) same amorphous) same	US-PGPUB;	17:43
		temperature) and @ad<20010829) and	EPO; JPO;	17.45
		438/\$3.ccls.	DERWENT	
-	169		USPAT;	2003/06/30
		with silicon	US-PGPUB;	17:11
			EPO; JPO;	
			DERWENT	
-	7		USPAT	2003/06/30
		"5966605"   "5998272"   "6225176"		17:29
		"6297115").PN.		0000 (05 (00
-	3	laser same silicon same amorphous same	USPAT;	2003/06/30
		wavelength same (pulse adj width) same	US-PGPUB;	17:45
		(irradiance or fluence) same (repetition adj rate)	EPO; JPO; DERWENT	
	19	1 3 ,	USPAT;	2003/06/30
_	19	width) same (irradiance or fluence) same	US-PGPUB;	17:50
		(repetition adj rate)	EPO; JPO;	- / • • •
		,	DERWENT	
-	12	(laser same wavelength same (pulse adj	USPAT;	2003/06/30
		width) same (irradiance or fluence) same	US-PGPUB;	18:20
		(repetition adj rate)) and @ad<20010829	EPO; JPO;	
			DERWENT	
-	10	((laser same wavelength same (pulse adj	USPAT;	2003/06/30
		width) same (irradiance or fluence) same	US-PGPUB;	17:46
		(repetition adj rate)) and @ad<20010829)	EPO; JPO;	
	202	not ultratech	DERWENT	2003/06/30
_	293	laser and wavelength and (pulse adj width) and (irradiance or fluence) and	USPAT; US-PGPUB;	17:50
		(repetition adj rate)	EPO; JPO;	17.30
		(repetition and rate)	DERWENT	
_	0	((((laser same gate same dop\$3 same	USPAT;	2003/06/30
	Ĭ	silicon) same amorphous) same	US-PGPUB;	17:51
	ĺ	temperature) and @ad<20010829) and (laser	EPO; JPO;	
		and wavelength and (pulse adj width) and	DERWENT	
		(irradiance or fluence) and (repetition		
		adj rate))		0000/05/55
-	1	(laser same gate same dop\$3 same silicon)	USPAT;	2003/06/30
		and (laser and wavelength and (pulse adj	US-PGPUB;	17:52
		width) and (irradiance or fluence) and	EPO; JPO; DERWENT	
1_	1	(repetition adj rate)) (melting with temperature with amorphous	USPAT;	2003/06/30
		with silicon) and (laser and wavelength	US-PGPUB;	17:52
		and (pulse adj width) and (irradiance or	EPO; JPO;	
		fluence) and (repetition adj rate))	DERWENT	
_	7	(laser and wavelength and (pulse adj	USPAT;	2003/06/30
		width) and (irradiance or fluence) and	US-PGPUB;	18:18
		(repetition adj rate)) and (dopant or	EPO; JPO;	
		impurity) and amorphous and silicon	DERWENT	0000/05/55
-	1416		USPAT;	2003/06/30
		silicon	US-PGPUB;	18:19
			EPO; JPO; DERWENT	
_	83	(diffus\$3 same amorphous same dop\$3 same	USPAT;	2003/06/30
-	63	silicon) same laser	US-PGPUB;	18:19
		SIII COM Same Idsel	EPO; JPO;	
			DERWENT	
-	1	(laser and wavelength and (pulse adj	USPAT;	2003/06/30
		width) and (irradiance or fluence) and	US-PGPUB;	18:20
		(repetition adj rate)) and ((diffus\$3	EPO; JPO;	
		same amorphous same dop\$3 same silicon)	DERWENT	
		same laser)		
-	72		USPAT;	2003/06/30
		silicon) same laser) and @ad<20010829	US-PGPUB;	18:21
			EPO; JPO;	
	1		DERWENT	1

	31	((diffus\$3 same amorphous same dop\$3 same	USPAT;	2003/06/30
		silicon) same laser) same gate	US-PGPUB;	18:21
		_	EPO; JPO;	
			DERWENT	
-	28	(((diffus\$3 same amorphous same dop\$3	USPAT;	2003/06/30
		same silicon) same laser) same gate) and	US-PGPUB;	19:18
		@ad<20010829	EPO; JPO;	
			DERWENT	
_	1	(dopant adj layer) with top with	USPAT;	2003/06/30
	_	(amorphous adj silicon)	US-PGPUB;	19:19
		( <u></u>	EPO; JPO;	
			DERWENT	
_	307	laser with (amorphous adj silicon) with	USPAT;	2003/06/30
		(dop\$3 or impurity)	US-PGPUB;	19:20
-		(dopts of imparity)	EPO; JPO;	13120
			DERWENT	
_	70	(laser with (amorphous adj silicon) with	USPAT;	2003/06/30
	, ,	(dop\$3 or impurity)) with gate	US-PGPUB;	19:20
	•	(dopys of imparity), with gate	EPO; JPO;	13.20
	l		DERWENT	
_	13	((laser with (amorphous adj silicon) with	USPAT;	2003/06/30
_	13	(dop\$3 or impurity)) with gate) same	US-PGPUB;	19:21
		temperature	EPO; JPO;	19.21
		temperature	DERWENT	
_	2	E009307 mm	USPAT;	2003/07/01
-		5908307.pn.	US-PGPUB;	15:08
				15:08
			EPO; JPO;	
		 	DERWENT	2003/07/01
_	4	wavelength same (temporal adj pulse adj	USPAT;	15:10
		width) same (irradiance or fluence)	US-PGPUB;	12:10
			EPO; JPO;	
	1.0		DERWENT	2002/07/01
_	10	(wavelength same (pulse adj width) same	USPAT;	2003/07/01
	1	(irradiance or fluence)) and (melt\$3 with	US-PGPUB;	15:10
		silicon)	EPO; JPO;	
			DERWENT	0000/07/01
-	129	wavelength same (pulse adj width) same	USPAT;	2003/07/01
		(irradiance or fluence)	US-PGPUB;	15:14
			EPO; JPO;	
			DERWENT	0000/10/20
-	2	6391731.pn.	USPAT;	2003/10/10
			EPO; JPO;	13:21
			DERWENT	